REQUEST FOR ACCESS OF ABANDONED APPLICATION UNDER 37 CFR 1.14(a)

•	In re Application of		
	Harari Et. Al.		
•	Application Number	per	Filed
	3375	lde	4/13/89
	Group Art Unit	Examiner	1
	233	ℓ	more
Assistant Commissioner for Patents Washington, DC 20231	·	Pap	er No
I hereby request access under 37 CFR 1.14(a identified ABANDONED application, which is:	(CHECK ONE)		
(A) referred to in United States Patent Nu	mber <u>5297</u>	148	, column,
(B) referred to in an application that is ope Application No, paper number,	en to public inspec , filed	tion as set forth in	n 37 CFR 1.11, i.e., n page of
(C) an application that claims the benefit o inspection, i.e., Application No	of the filing date of	an application th	at is open to public
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US005297148A

United States Patent [19]

Harari et al.

[56]

4,612,640

4,688,219 8/1987

[11] Patent Number:

5,297,148

[45] Date of Patent:

Mar. 22, 1994

[54]	FLASH EE	PROM SYSTEM
[75]	Inventors:	Eliyahou Harari, Los Gatos; Robert D. Norman, San Jose; Sanjay Mehrotra, Milpitas, all of Calif.
[73]	Assignee:	SunDisk Corporation, Santa Clara, Calif.
[21]	Appl. No.:	963,838
[22]	Filed:	Oct. 20, 1992
	Rela	ted U.S. Application Data
[62]	Division of doned.	Ser. No. 337,566, Apr. 13, 1989, aban-
[51]		G06F 11/00
[52]	U.S. Cl	371/10.2; 371/10.1;
		371/10.3; 365/200
[58]	Field of Sea	arch 371/10.2, 10.1, 10.3,
		371/40 1: 365/200

References Cited

U.S. PATENT DOCUMENTS

4,601,031 7/1986 Walker et al. 371/10.3

9/1986 Mehrotra et al. 371/40.1

Takemae 371/10.3

4,796,233	1/1989	Awaya et al 371/10.2
4,920,518	4/1990	Nakamura et al 371/10.2
4,949,309	8/1990	Rao 365/218

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[57] ABSTRACT

A system of Flash EEprom memory chips with controlling circuits serves as non-volatile memory such as that provided by magnetic disk drives. Improvements include selective multiple sector erase, in which any combinations of Flash sectors may be erased together. Selective sectors among the selected combination may also be de-selected during the erase operation. Another improvement is the ability to remap and replace defective cells with substitute cells. The remapping is performed automatically as soon as a defective cell is detected. When the number of defects in a Flash sector becomes large, the whole sector is remapped. Yet another improvement is the use of a write cache to reduce the number of writes to the Flash EEprom memory, thereby minimizing the stress to the device from undergoing too many write/erase cycling.

4 Claims, 5 Drawing Sheets

